DISCRETE SEMICONDUCTORS

DATA SHEET



PRLL5817; PRLL5818; PRLL5819 Schottky barrier diodes

Product data sheet Supersedes data of 1996 May 03 1999 Apr 22



Schottky barrier diodes

PRLL5817; PRLL5818; PRLL5819

FEATURES

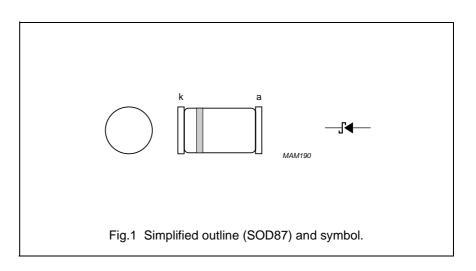
- · Low switching losses
- · Fast recovery time
- · Guard ring protected
- Hermetically sealed glass SMD package.

APPLICATIONS

- Low power, switched-mode power supplies
- Rectifying
- · Polarity protection.



The PRLL5817 to PRLL5819 types are Schottky barrier diodes fabricated in planar technology, and encapsulated in SOD87 hermetically sealed glass SMD packages incorporating Implotec^{TM(1)} technology.



MARKING

TYPE NUMBER	MARKING CODE
PRLL5817	9
PRLL5818	9
PRLL5819	9

⁽¹⁾ Implotec is a trademark of Philips.

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PRLL5817; PRLL5818; PRLL5819

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _R	continuous reverse voltage				
	PRLL5817		_	20	V
	PRLL5818		_	30	V
	PRLL5819		_	40	V
V_{RSM}	non-repetitive peak reverse voltage				
	PRLL5817		_	24	V
	PRLL5818		_	36	V
	PRLL5819		_	48	V
V_{RRM}	repetitive peak reverse voltage				
	PRLL5817		_	20	V
	PRLL5818		_	30	V
	PRLL5819		_	40	V
V_{RWM}	crest working reverse voltage				
	PRLL5817		_	20	V
	PRLL5818		_	30	V
	PRLL5819		_	40	V
I _{F(AV)}	average forward current	T _{amb} = 60 °C	_	1	Α
I _{FSM}	non-repetitive peak forward current	t = 10 ms half sine wave; $T_j = T_{j \text{ max}}$ prior to surge: $V_R = 0$	_	25	А
T _{stg}	storage temperature		-65	+175	°C
Tj	junction temperature		_	125	°C

Schottky barrier diodes

PRLL5817; PRLL5818; PRLL5819

ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	forward voltage	see Fig.2				
	PRLL5817	I _F = 0.1 A	_	_	320	mV
		I _F = 1 A	_	_	450	mV
		I _F = 3 A	_	_	750	mV
V _F	forward voltage	see Fig.2				
	PRLL5818	I _F = 0.1 A	_	_	330	mV
		I _F = 1 A	_	_	550	mV
		I _F = 3 A	_	_	875	mV
V _F	forward voltage	see Fig.2				
	PRLL5819	I _F = 0.1 A	_	_	340	mV
		I _F = 1 A	_	_	600	mV
		I _F = 3 A	_	_	900	mV
I _R	reverse current	V _R = V _{RRMmax} ; note 1	_	0.5	1	mA
		$V_R = V_{RRMmax}$; $T_j = 100 ^{\circ}C$	_	5	10	mA
C _d	diode capacitance	V _R = 4 V; f = 1 MHz				
	PRLL5817		_	70	_	pF
	PRLL5818		_	50	_	pF
	PRLL5819		_	50	_	pF

Note

1. Pulse test: t_p = 300 μ s; δ = 0.02.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	note 1	150	K/W

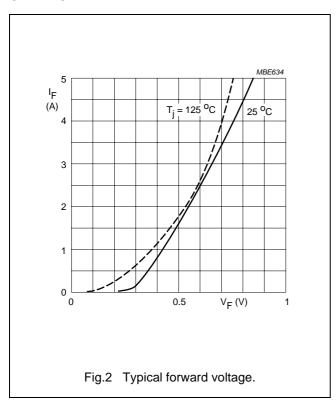
Note

1. Refer to SOD87 standard mounting conditions.

Schottky barrier diodes

PRLL5817; PRLL5818; PRLL5819

GRAPHICAL DATA



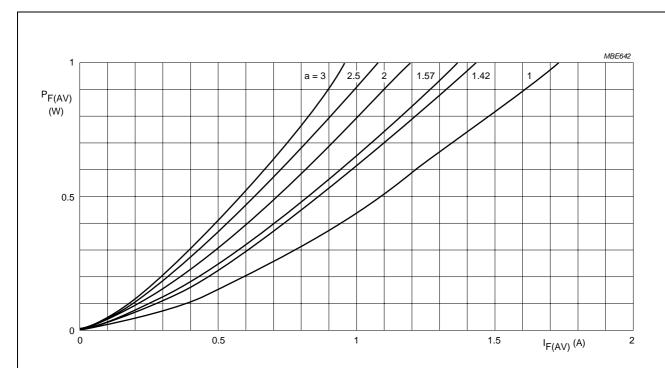


Fig.3 PRLL817. Maximum values steady state forward power dissipation as a function of the average forward current; $a = I_{F(RMS)}/I_{F(AV)}$.

1999 Apr 22

Schottky barrier diodes

PRLL5817; PRLL5818; PRLL5819

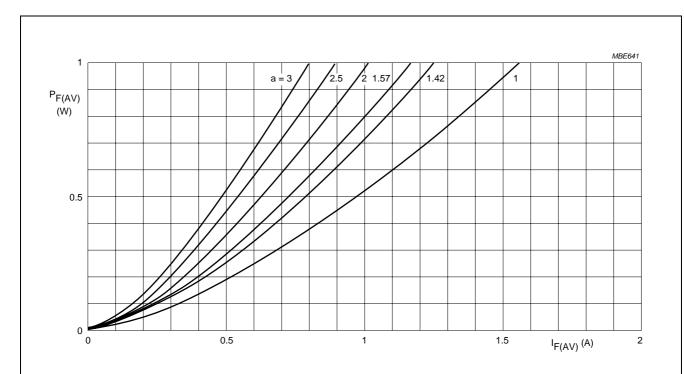


Fig.4 PRLL5818. Maximum values steady state forward power dissipation as a function of the average forward current; $a = I_{F(RMS)}/I_{F(AV)}$.

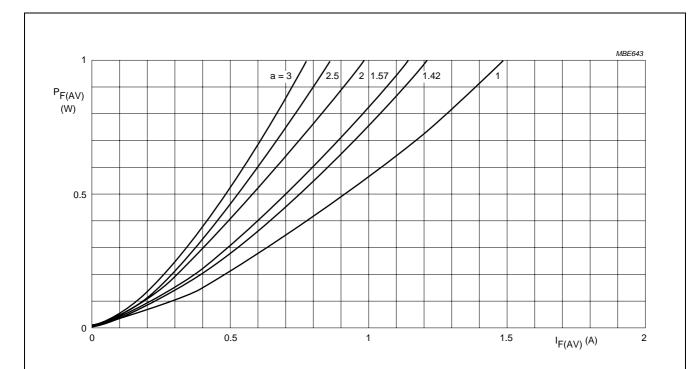


Fig.5 PRLL5819. Maximum values steady state forward power dissipation as a function of the average forward current; $a = I_{F(RMS)}/I_{F(AV)}$.

6

1999 Apr 22

Schottky barrier diodes

PRLL5817; PRLL5818; PRLL5819

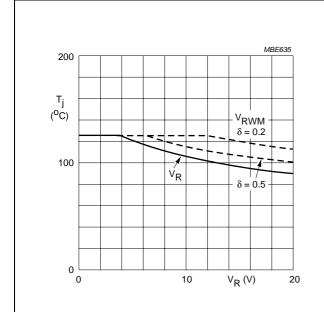


Fig.6 PRLL5817. Maximum permissible junction temperature as a function of reverse voltage; device mounted; refer to SOD87 standard mounting conditions.

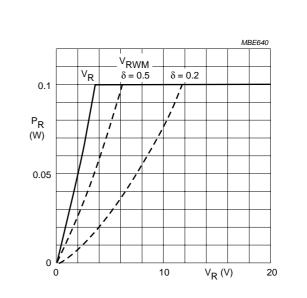


Fig.7 PRLL5817. Reverse power dissipation as a function of reverse voltage (max. values); device mounted; refer to SOD87 standard mounting conditions.

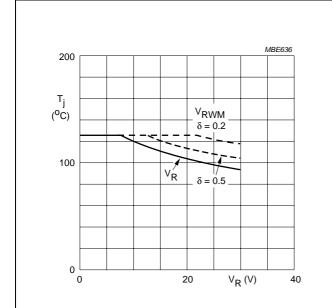


Fig.8 PRLL5818. Maximum permissible junction temperature as a function of reverse voltage; device mounted; refer to SOD87 standard mounting conditions.

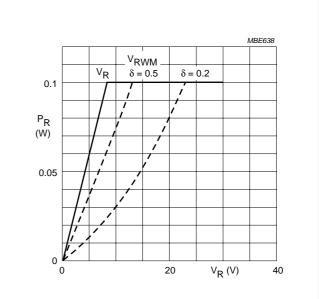


Fig.9 PRLL5818. Reverse power dissipation as a function of reverse voltage (max. values); device mounted; refer to SOD87 standard mounting conditions.

Schottky barrier diodes

PRLL5817; PRLL5818; PRLL5819

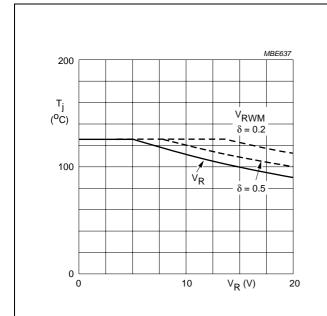


Fig.10 PRLL5819. Maximum permissible junction temperature as a function of reverse voltage; device mounted; refer to SOD87 standard mounting conditions.

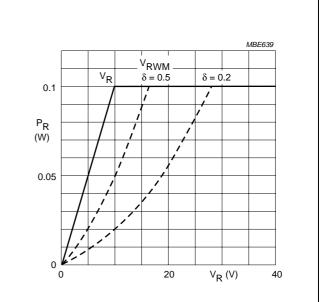


Fig.11 PRLL5819. Reverse power dissipation as a function of reverse voltage (max. values); device mounted; refer to SOD87 standard mounting conditions.

Schottky barrier diodes

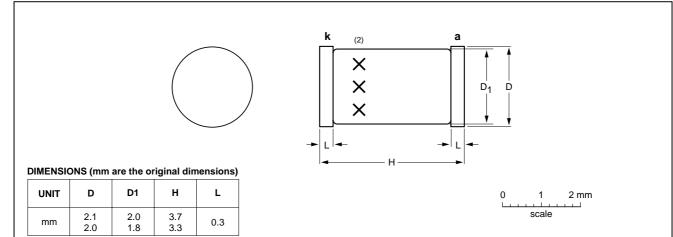
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PACKAGE OUTLINE

Hermetically sealed glass surface mounted package;

Implotec^{TM(1)} technology; 2 connectors

SOD87



Notes

- 1. Implotec is a trademark of Philips.
- 2. The marking indicates the cathode.

OUTLINE	REFERENCES			EUROPEAN	ICCUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION ISSUE DATE	
SOD87	100H03					-99-03-31 99-06-04

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

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